Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

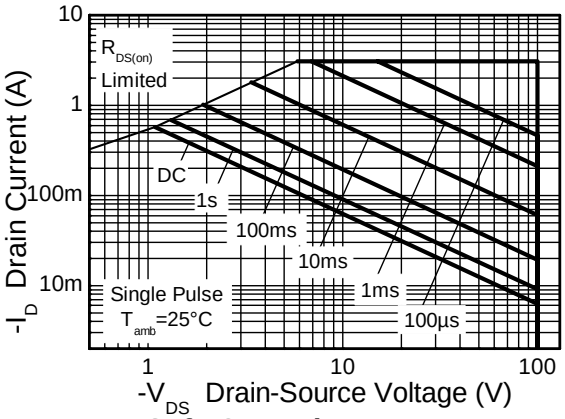
Characteristic				Symbol	Value	Units
Drain-Source Voltage				V_{DSS}	-100	V
Gate-Source Voltage				V_{GS}	±20	V
Continuous Drain Current	V_{GS} = 10V	T_A = +70°C	(Note 6) (Note 6) (Note 6)	I_D	-0.7 -0.5 -0.6	A
Pulsed Drain Current (Note 7)				I_{DM}	-3.1	A
Continuous Source Current (Body Diode) (Note 5)				I_S	-1.1	A
Pulsed Source Current (Body Diode) (Note 7)				I_{SM}	-3.1	A

Thermal Characteristics

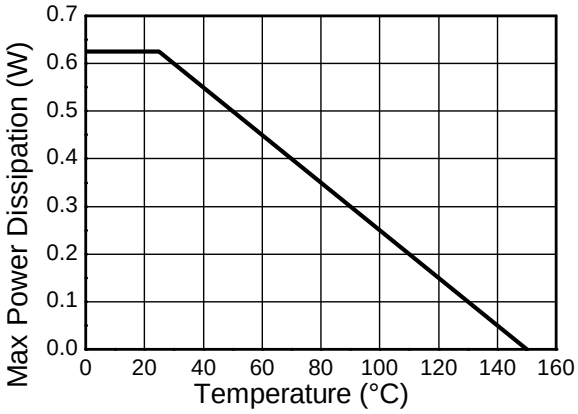
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Linear Derating Factor	P_D	625 5	mW mW/°C
Power Dissipation (Note 6) Linear Derating Factor	P_D	806 6.4	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	155	°C/W
Thermal Resistance, Junction to Leads (Note 8)	$R_{\theta JL}$	194	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Notes:
5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
6. For a device surface mounted on FR4 PCB measured at t ≤5 secs.
7. Repetitive rating 25mm x 25mm FR4 PCB, D=0.05 pulse width=10µs - pulse current limited by maximum junction temperature.
8. Thermal resistance from junction to solder-point (at the end of the drain lead).

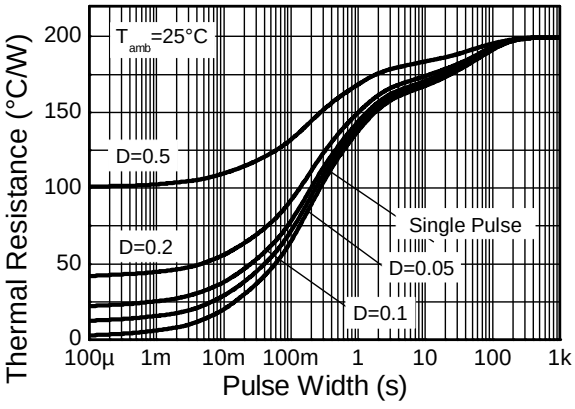
Thermal Characteristics (Continued)



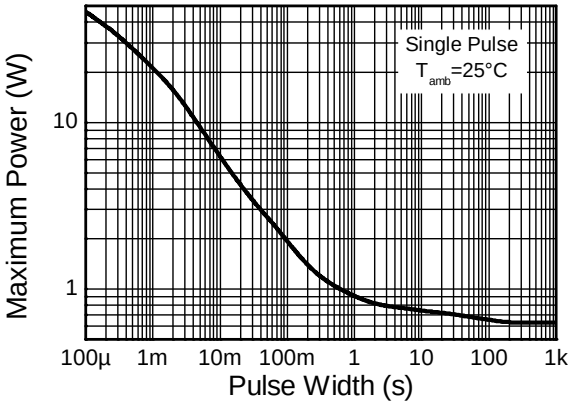
Safe Operating Area



Derating Curve



Transient Thermal Impedance



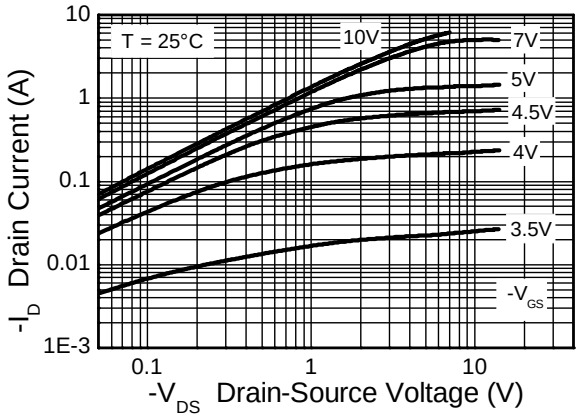
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

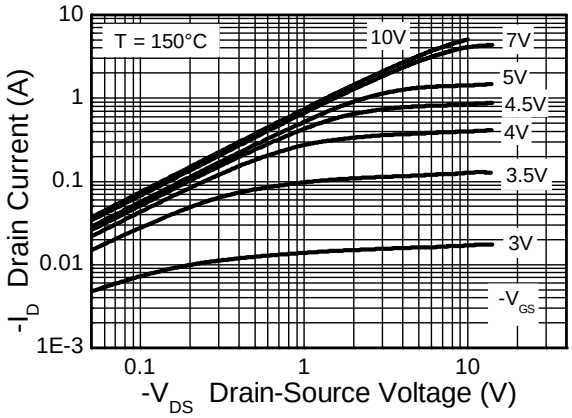
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	-100	—	—	V	I_D = -250µA, V_{GS} = 0V
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1.0	µA	V_{DS} = -100V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	-2.0	—	-4.0	V	I_D = -250µA, V_{DS} = V_{GS}
Static Drain-Source On-Resistance (Note 9)	$R_{DS(ON)}$	—	—	1.0	Ω	V_{GS} = -10V, I_D = -0.6A
				1.45		V_{GS} = -6.0V, I_D = -0.5A
Forward Transconductance (Notes 9 & 11)	g_{FS}	—	1.2	—	S	V_{DS} = -15V, I_D = -0.6A
Diode Forward Voltage (Note 9)	V_{SD}	—	-0.85	-0.95	V	T_J = +25°C, I_S = -0.75A, V_{GS} = 0V
Reverse Recovery Time (Note 11)	t_{RR}	—	29	—	ns	T_J = +25°C, I_F = -0.9A, di/dt = 100A/µs
Reverse Recovery Charge (Note 11)	Q_{RR}	—	31	—	nC	
DYNAMIC CHARACTERISTICS (Note 11)						
Input Capacitance	C_{ISS}	—	141	—	pF	V_{DS} = -50V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{OSS}	—	13.1	—		
Reverse Transfer Capacitance	C_{RSS}	—	10.8	—		
Turn-On Delay Time (Note 10)	$t_{D(ON)}$	—	1.6	—	ns	V_{DD} = -50V, I_D = -1.0A, $R_G \cong 6.0\Omega$, V_{GS} = -10V
Turn-On Rise Time (Note 10)	t_R	—	2.1	—		
Turn-Off Delay Time (Note 10)	$t_{D(OFF)}$	—	5.9	—		
Turn-Off Fall Time (Note 10)	t_F	—	3.3	—		
Total Gate Charge (Note 10)	Q_G	—	1.8	—	nC	V_{DS} = -50V, V_{GS} = -5.0V, I_D = -0.6A
Total Gate Charge (Note 10)	Q_G	—	3.5	—	nC	V_{DS} = -50V, V_{GS} = -10V, I_D = -0.6A
Gate-Source Charge (Note 10)	Q_{GS}	—	0.6	—		
Gate-Drain Charge (Note 10)	Q_{GD}	—	1.6	—		

Notes: 9. Measured under pulsed conditions. Pulse width = 300µs. Duty cycle ≤ 2%.
10. Switching characteristics are independent of operating junction temperature.
11. For design aid only, not subject to production testing.

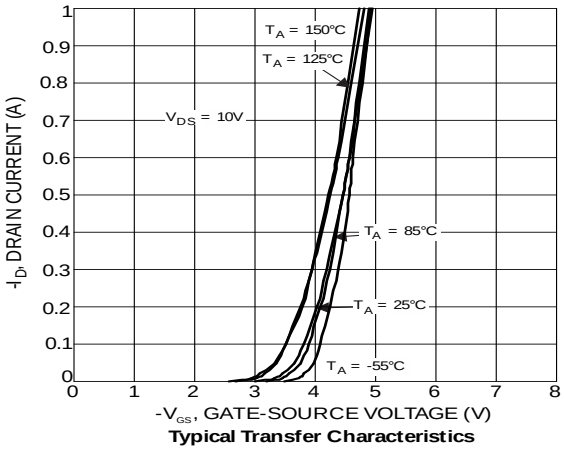
Typical Characteristics



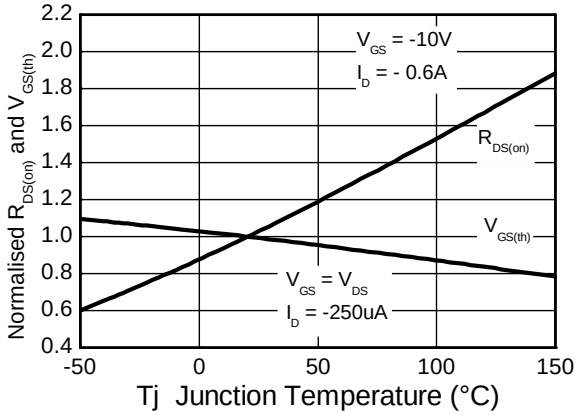
Output Characteristics



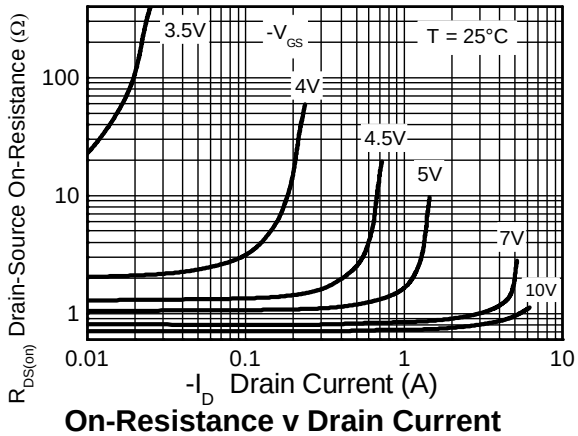
Output Characteristics



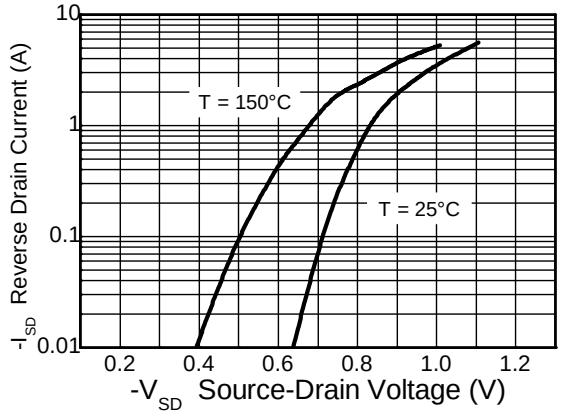
Typical Transfer Characteristics



Normalised Curves v Temperature

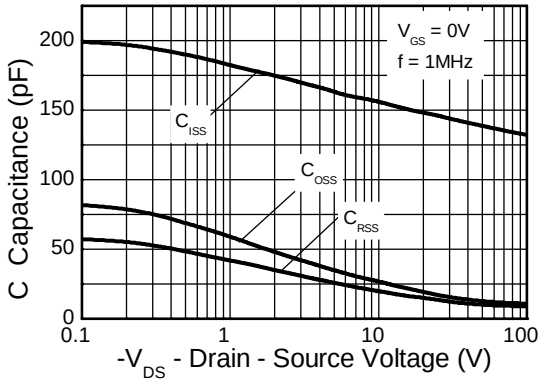


On-Resistance v Drain Current

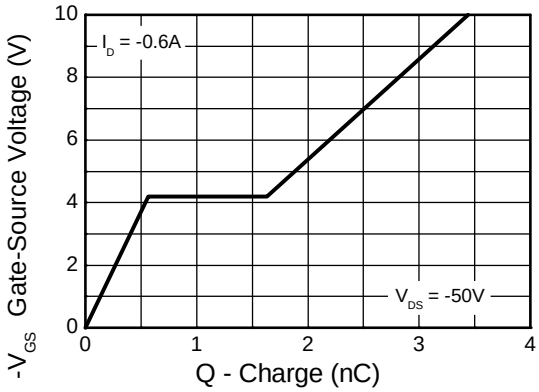


Source-Drain Diode Forward Voltage

Typical Characteristics (Continued)

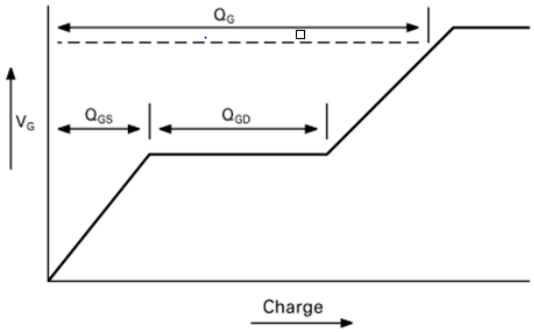


Capacitance v Drain-Source Voltage

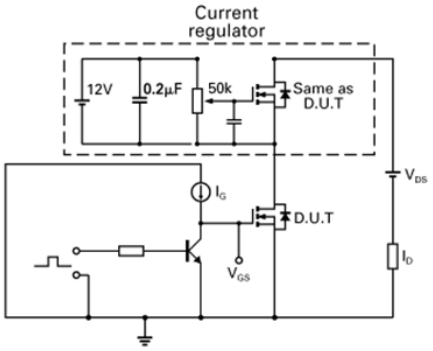


Gate-Source Voltage v Gate Charge

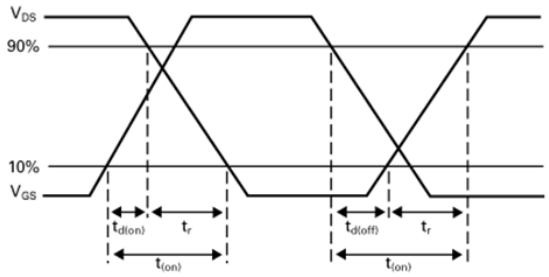
Test Circuits



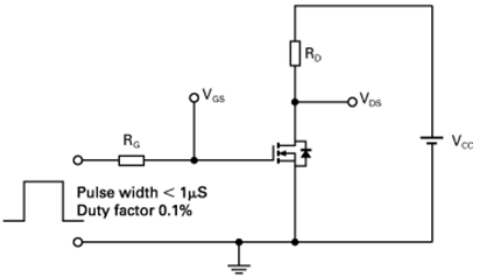
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

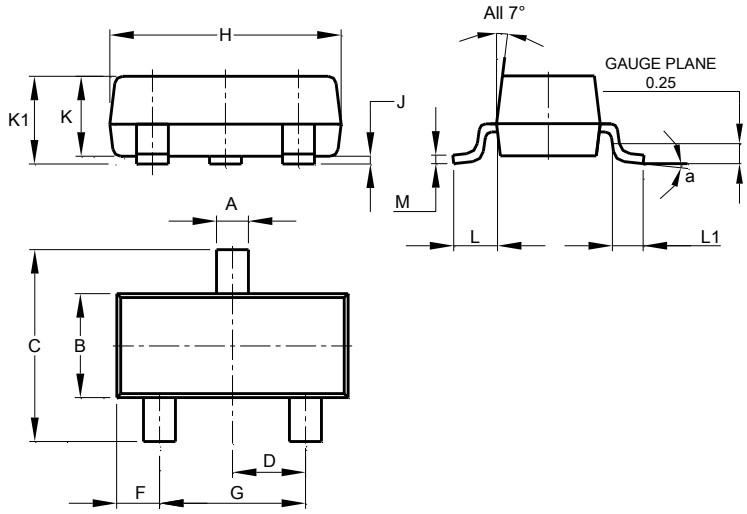


Switching time test circuit

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

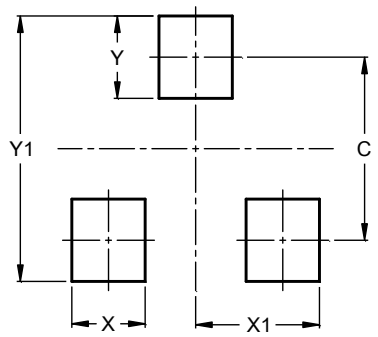


SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	–
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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